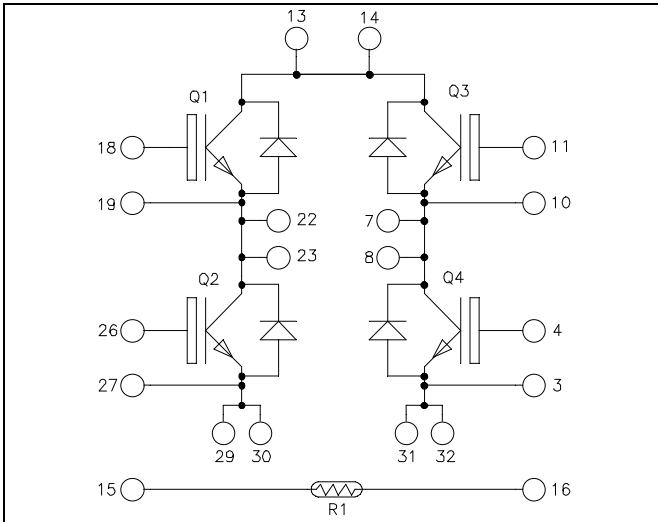


**Full - Bridge
Trench + Field Stop IGBT3
Power Module**

**$V_{CES} = 600V$
 $I_C = 75A @ T_c = 80^\circ C$**

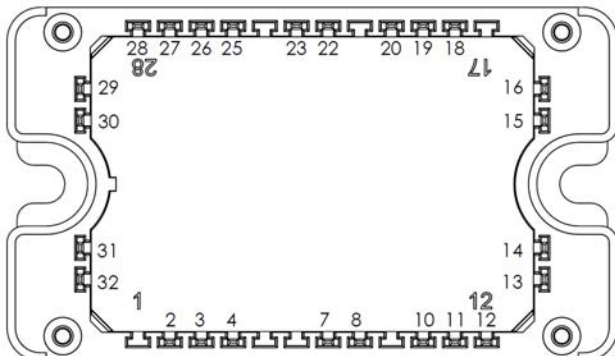


Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- **Trench + Field Stop IGBT3**
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of V_{CESat}
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS compliant

All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	100
		$T_C = 80^\circ C$	75
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	140
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Power Dissipation	$T_C = 25^\circ C$	250
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	150A @ 550V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (per IGBT)

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 75A$	$T_j = 25^\circ C$	1.5	1.9	V
			$T_j = 150^\circ C$	1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 600\mu A$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

Dynamic Characteristics (per IGBT)

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{ies}	Input Capacitance	$V_{GE} = 0V$		4620		pF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		300		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		140		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ($25^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 75A$ $R_G = 4.7\Omega$		110		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			200		
T_f	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ($150^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 75A$ $R_G = 4.7\Omega$		120		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			250		
T_f	Fall Time			60		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 75A$	$T_j = 25^\circ C$	0.35		mJ
			$T_j = 150^\circ C$	0.6		
E_{off}	Turn-off Switching Energy	$R_G = 4.7\Omega$	$T_j = 25^\circ C$	2.2		mJ
			$T_j = 150^\circ C$	2.6		
R_{thJC}	Junction to Case Thermal Resistance				0.6	$^\circ C/W$

Reverse diode ratings and characteristics (per diode)

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V_{RRM}	Peak Repetitive Reverse Voltage				600	V
I_{RM}	Reverse Leakage Current	$V_R = 600V$			250	μA
I_F	DC Forward current		$T_c = 40^\circ C$	75		A
V_F	Diode Forward Voltage	$I_F = 75A$ $V_{GE} = 0V$	$T_j = 25^\circ C$	1.6	2	V
			$T_j = 150^\circ C$	1.5		
t_{rr}	Reverse Recovery Time	$I_F = 75A$ $V_R = 300V$ $di/dt = 2000A/\mu s$	$T_j = 25^\circ C$	100		ns
			$T_j = 150^\circ C$	150		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ C$	3.6		μC
			$T_j = 150^\circ C$	7.6		
E_r	Reverse Recovery Energy		$T_j = 25^\circ C$	0.85		mJ
			$T_j = 150^\circ C$	1.8		
R_{thJC}	Junction to Case Thermal Resistance				0.98	$^\circ C/W$

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

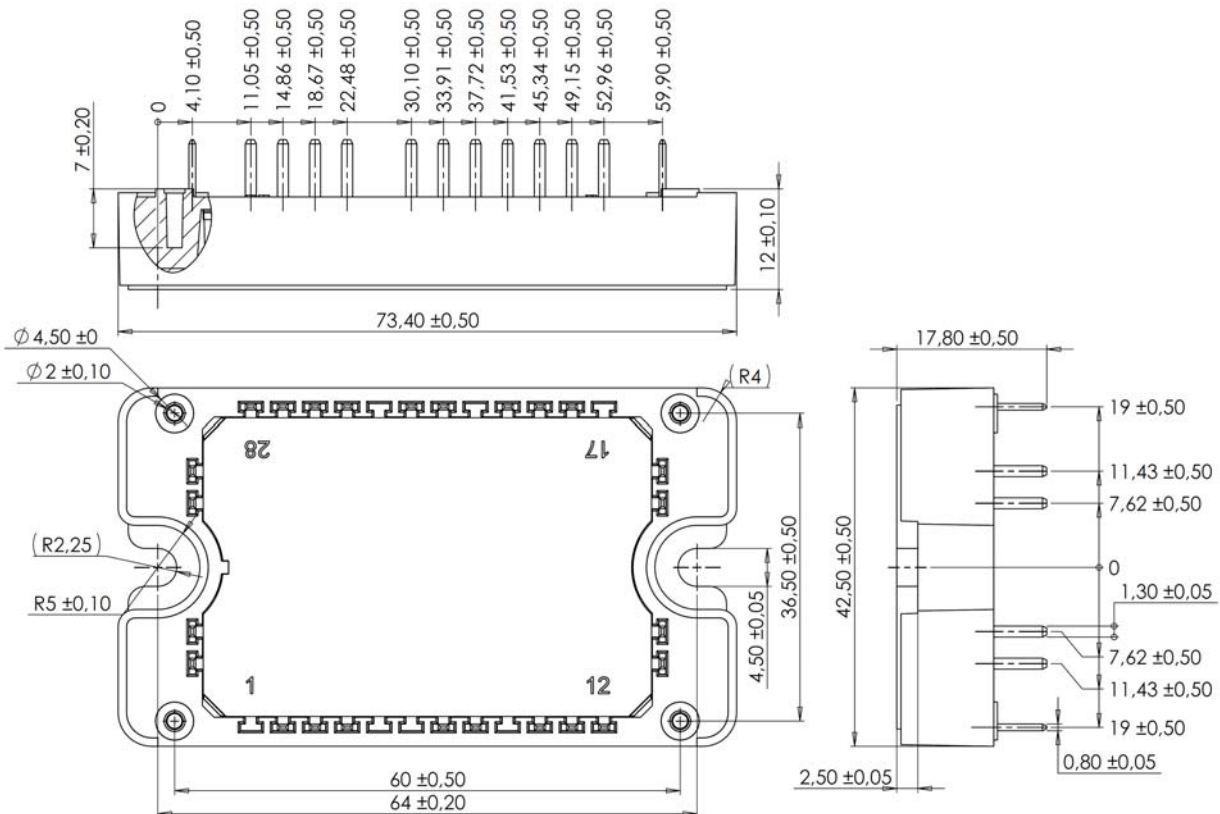
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

Thermal and package characteristics

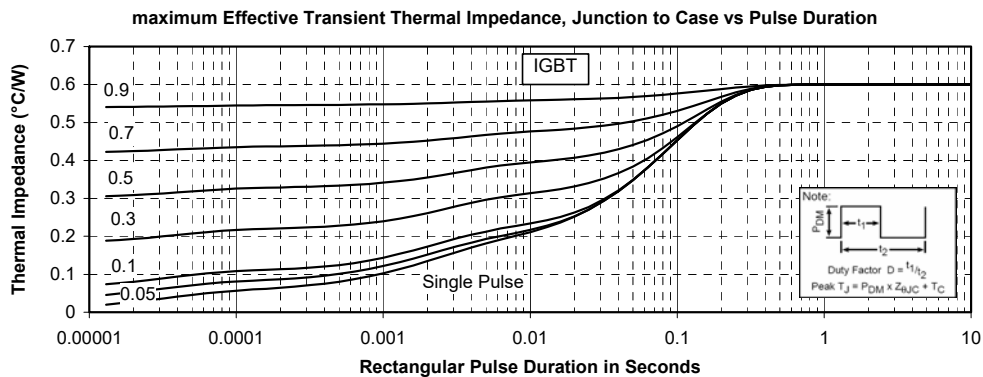
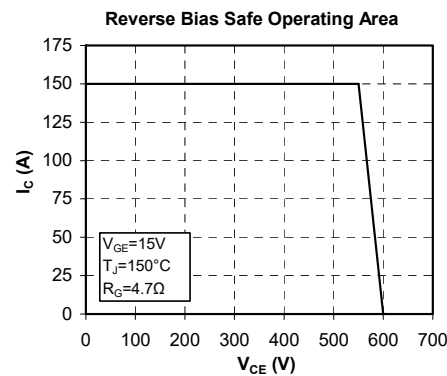
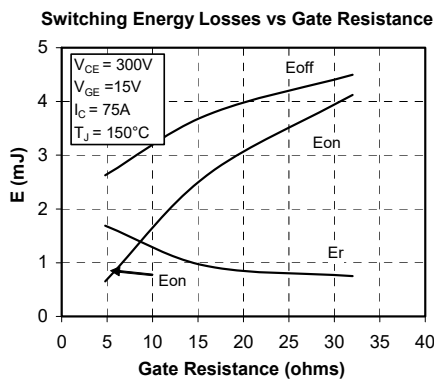
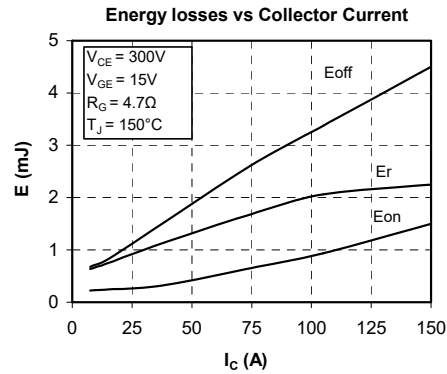
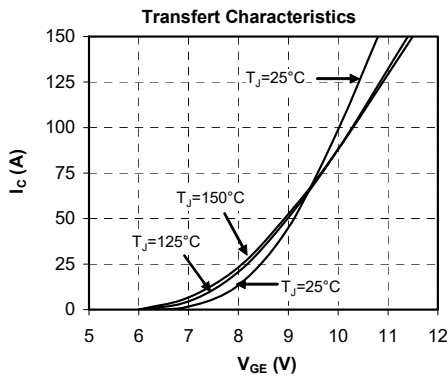
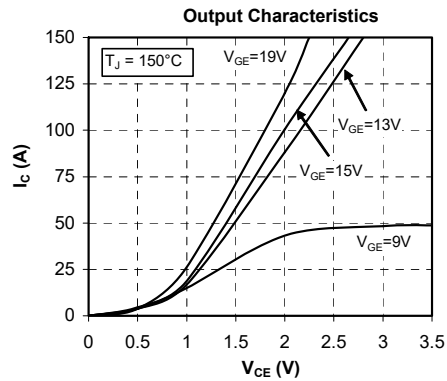
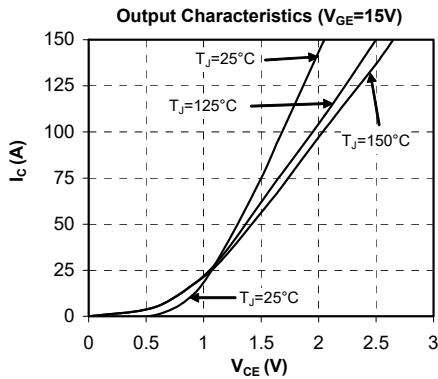
Symbol	Characteristic	Min	Max	Unit		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000		V		
T _J	Operating junction temperature range	-40	175	°C		
T _{JOP}	Recommended junction temperature under switching conditions	-40	T _{Jmax} -25			
T _{STG}	Storage Temperature Range	-40	125			
T _C	Operating Case Temperature	-40	125			
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

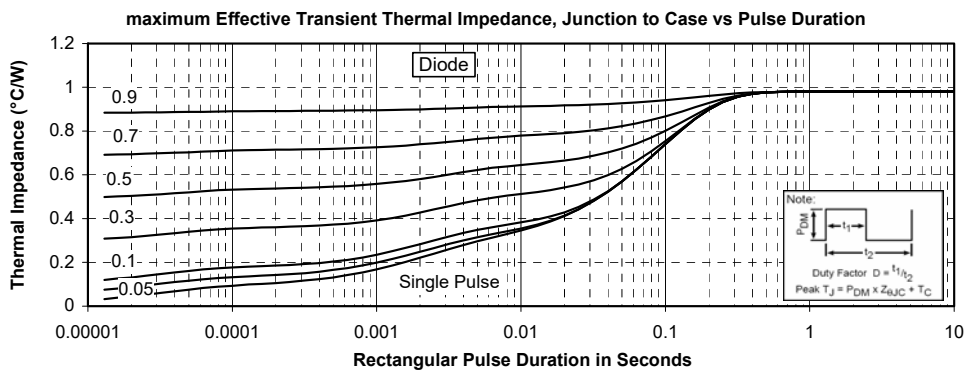
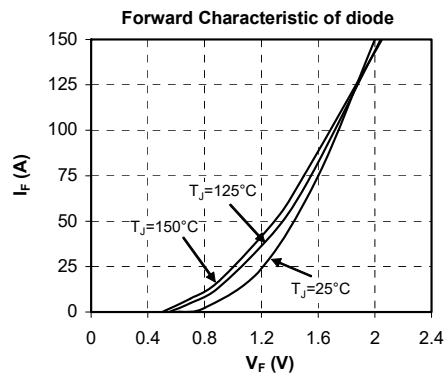
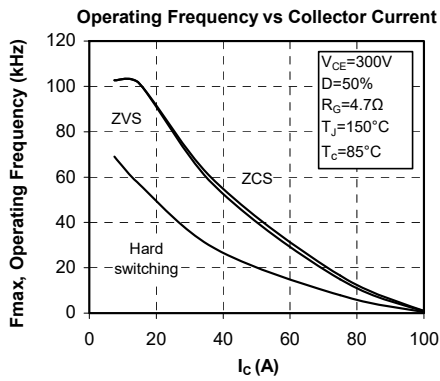
Package outline (dimensions in mm)



See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

Typical Performance Curve





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